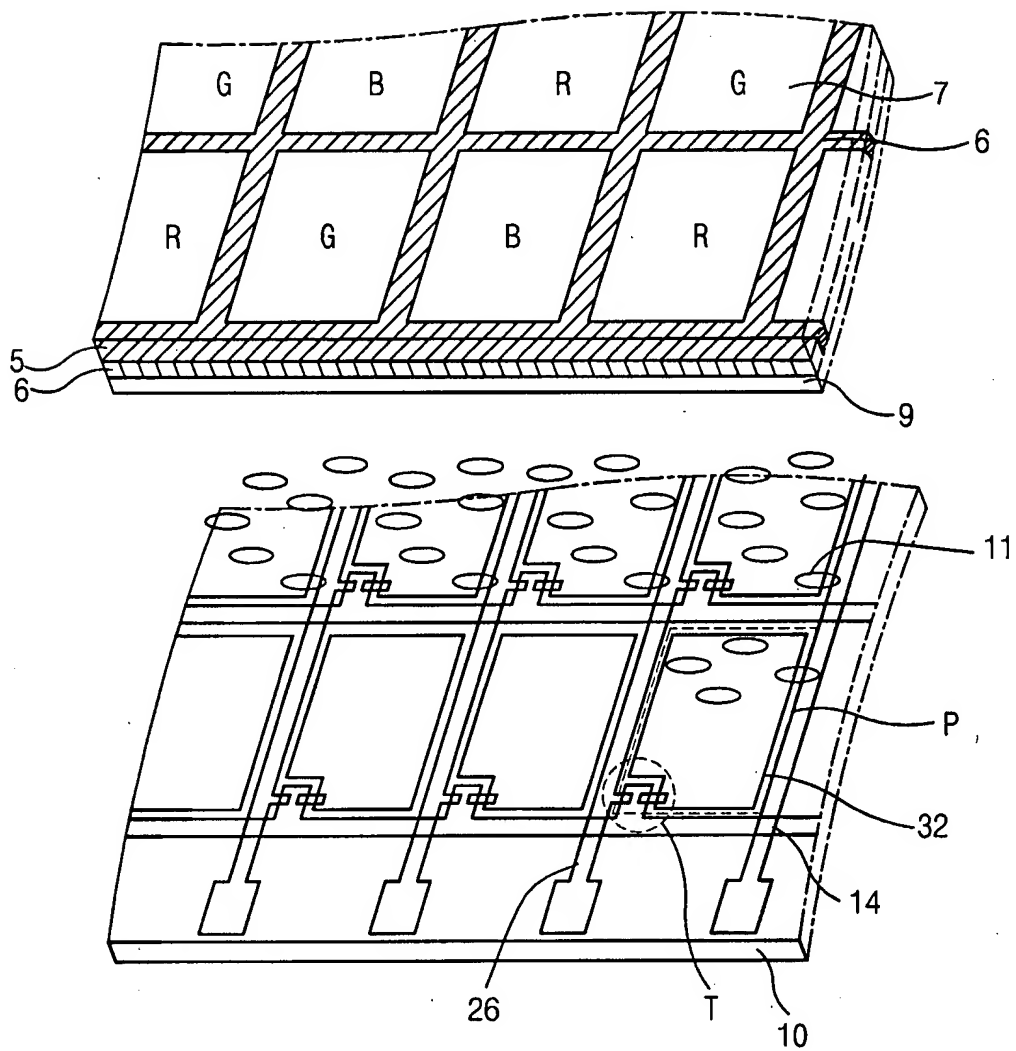


FIG. 1
RELATED ART



-P

10

14

14

$$\begin{pmatrix} 18c \\ 18a \\ 18b \end{pmatrix} 18$$

(

24

ト

A

22

IV

FIG. 3
RELATED ART

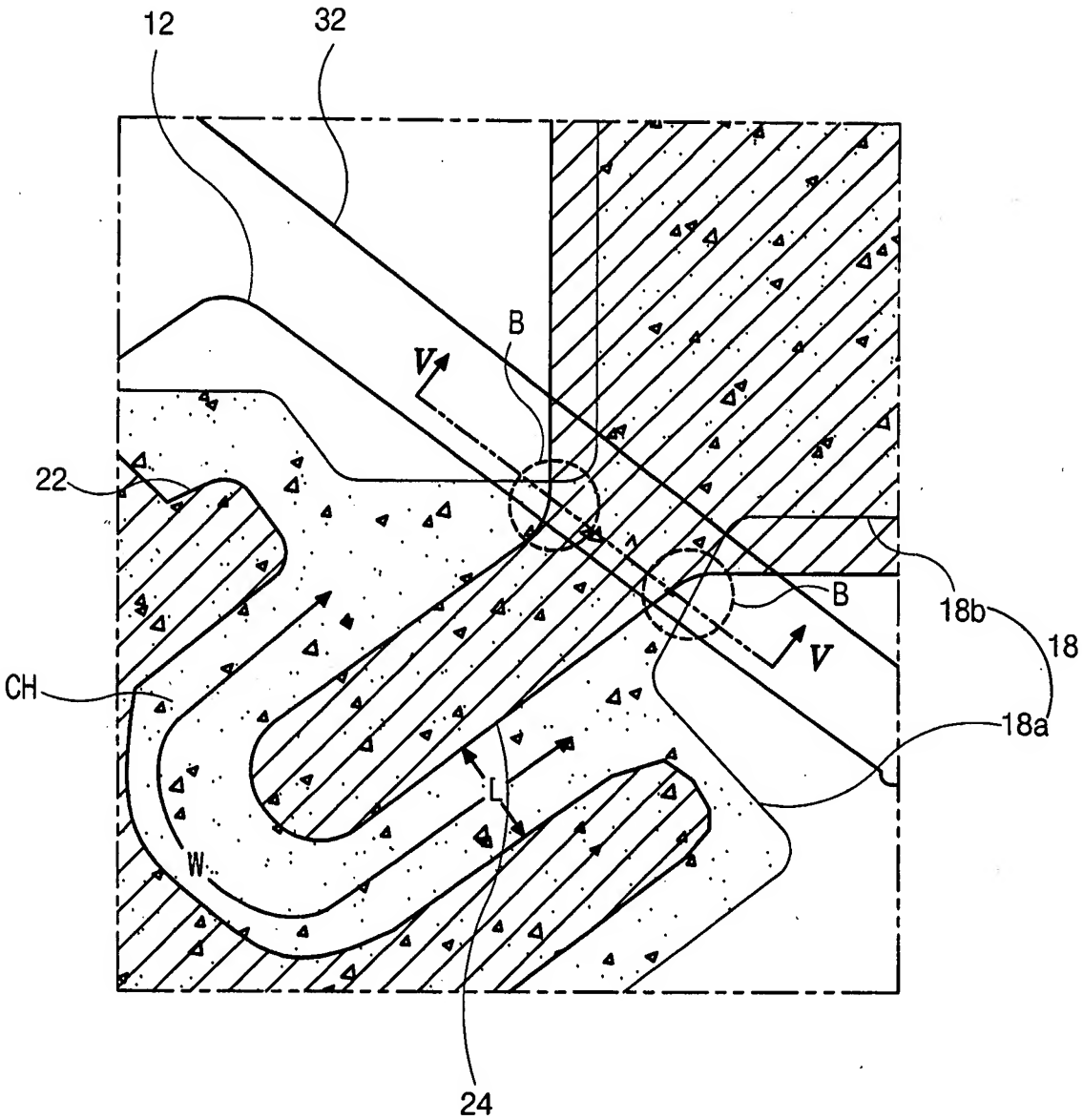


FIG. 4A
RELATED ART

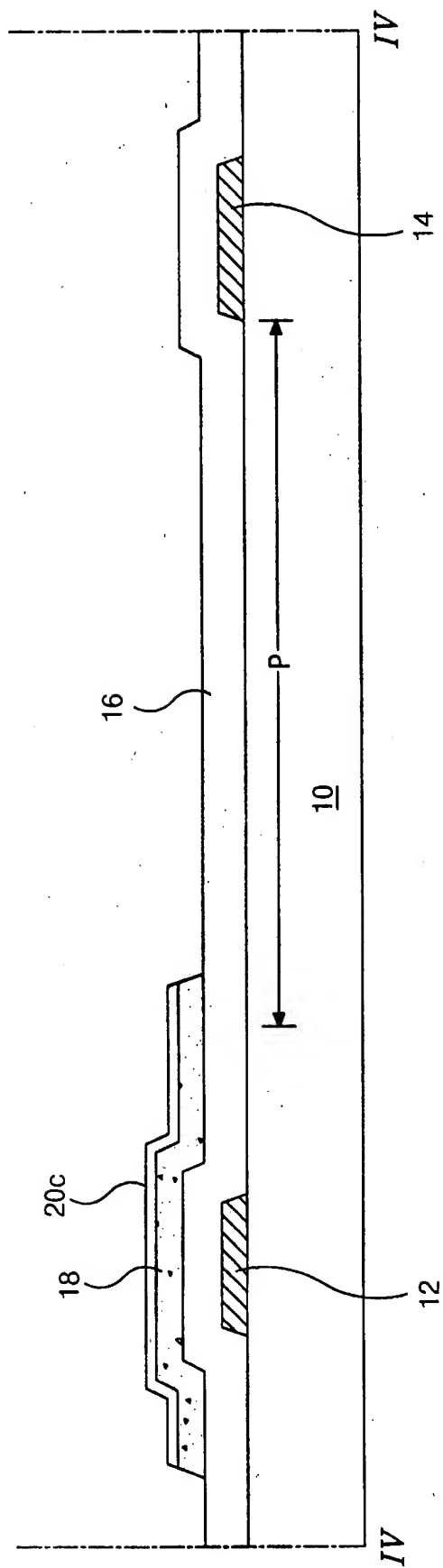
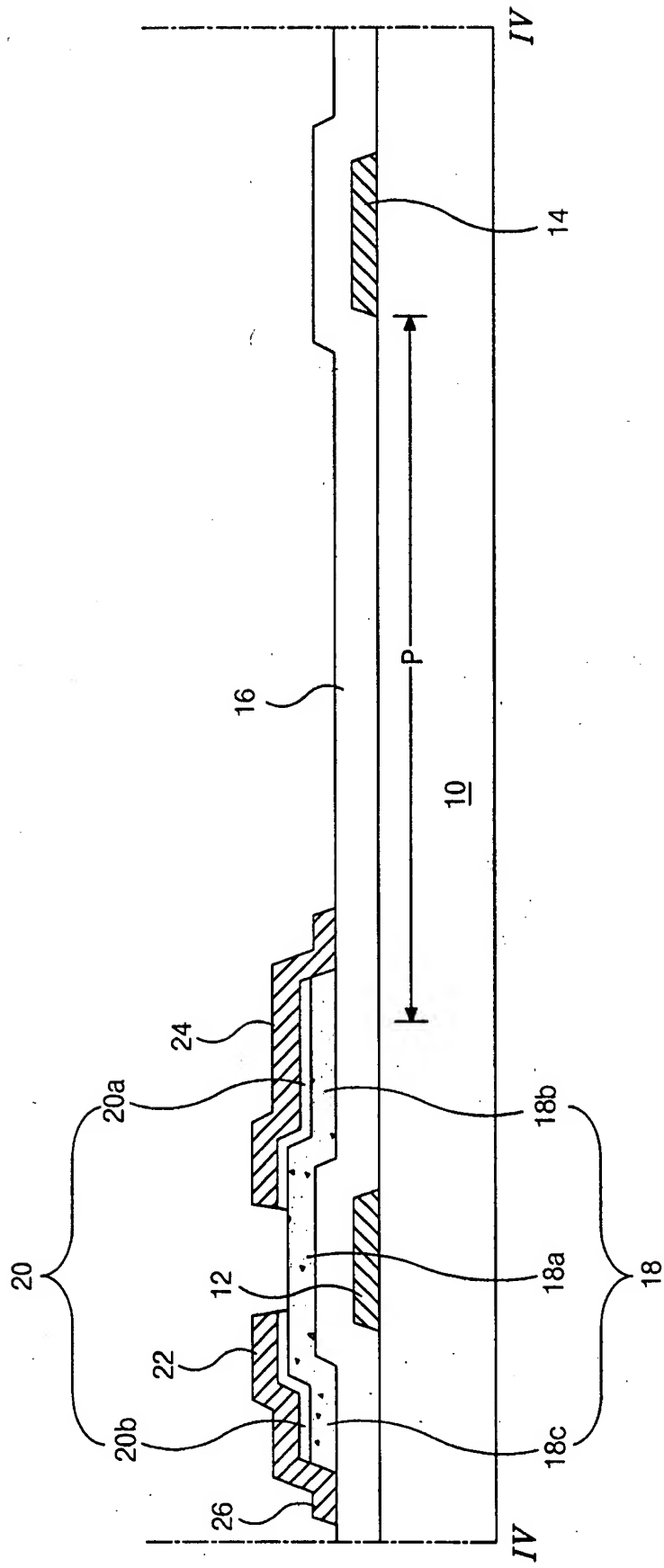


FIG. 4B
RELATED ART



This cross-sectional view shows the device 10 along line IV-IV. It features a substrate 14 with a top layer 16. A central region 12 is filled with a material 20, which is divided into sub-regions 20a, 20b, and 20c. These sub-regions are separated by vertical walls 22 and 24. A layer 26 is located at the bottom of the central region. A layer 28 is positioned above the central region. A layer 30 is located on the right side of the device. A dimension line 10 indicates the width of the central region. A dimension line P indicates the pitch of the structure. A dimension line l indicates the thickness of the top layer 16. The device is labeled 10.

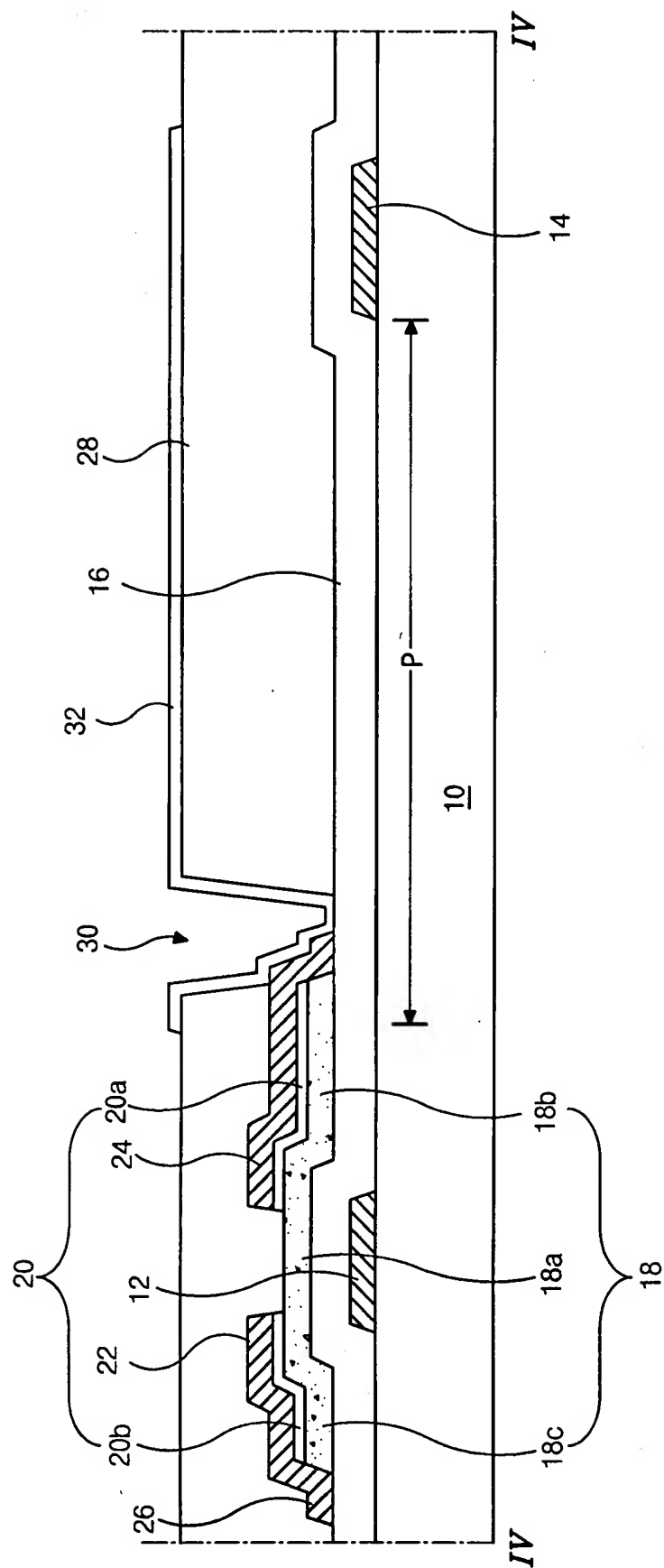


FIG. 5A
RELATED ART

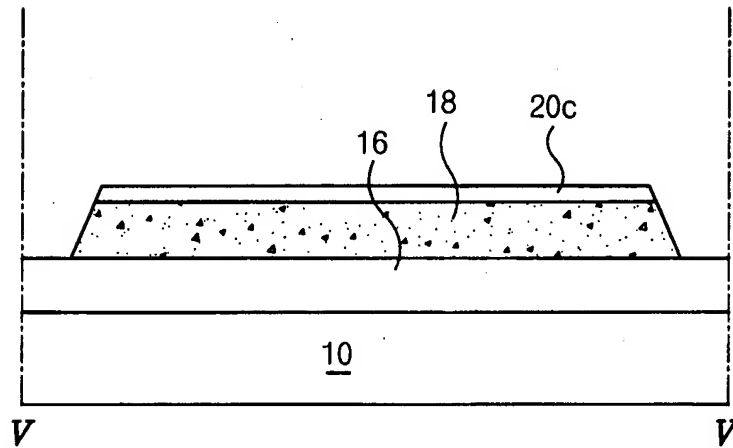


FIG. 5B
RELATED ART

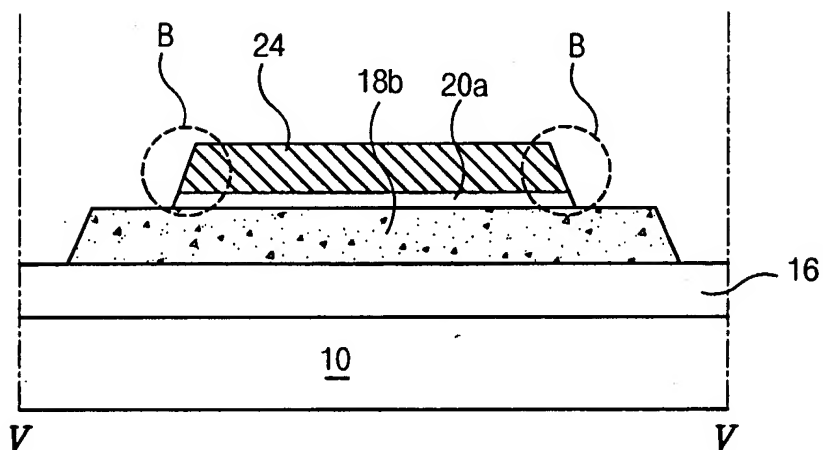


FIG. 5C
RELATED ART

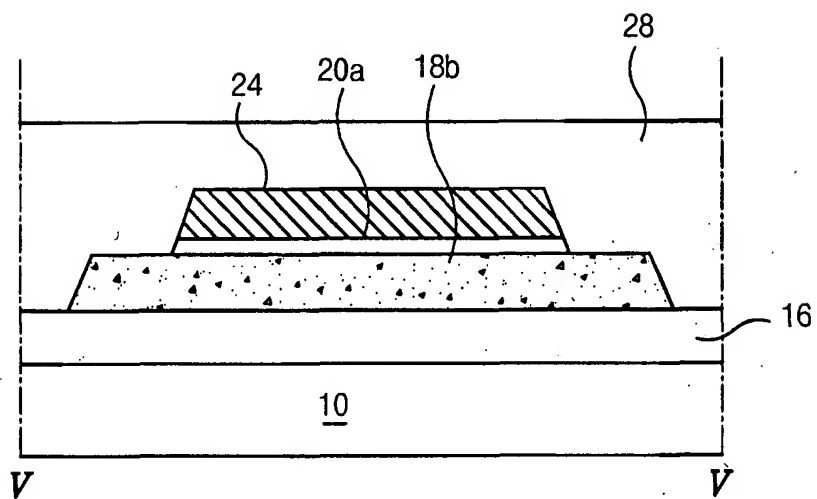


FIG. 6

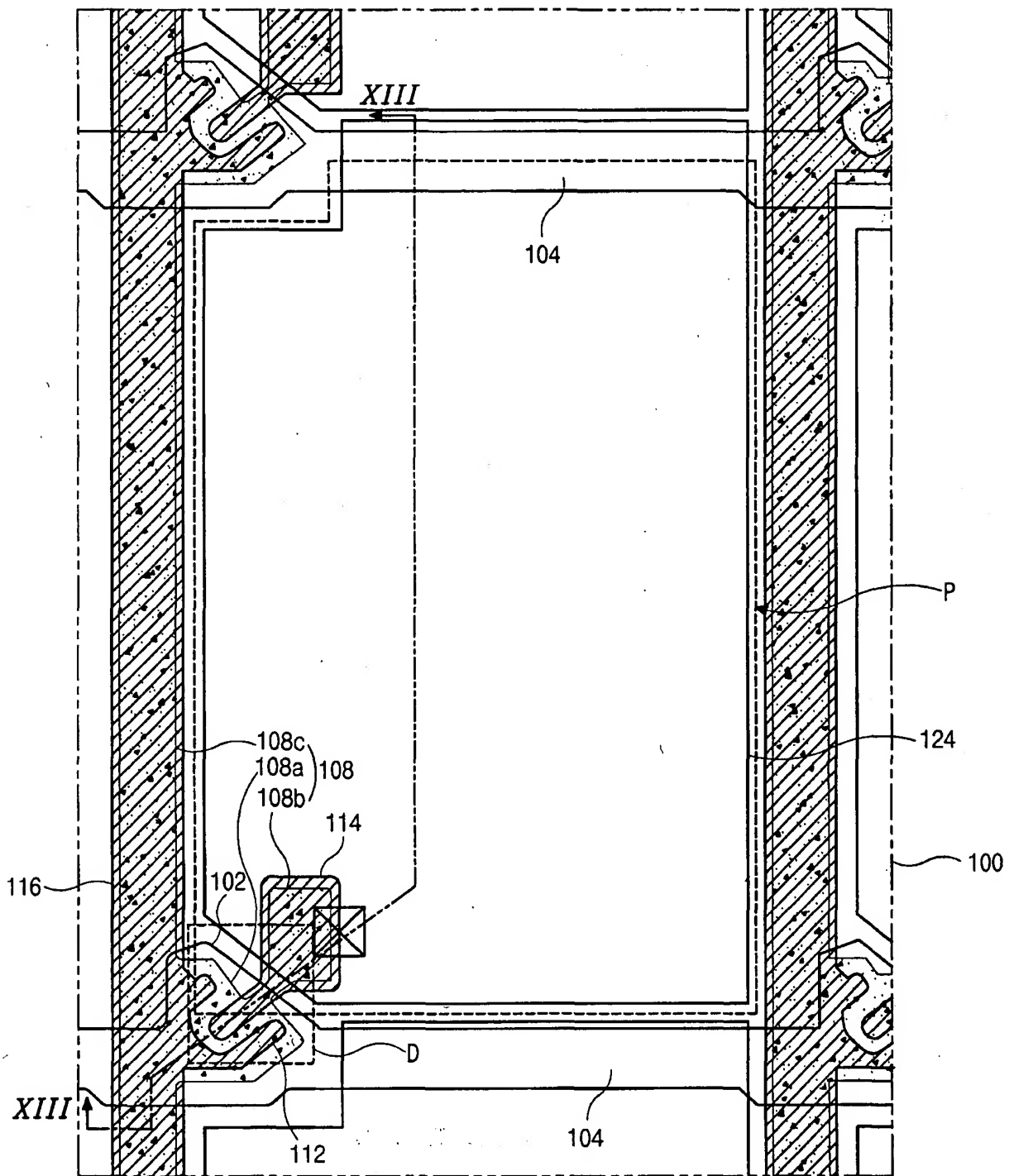


FIG. 8A

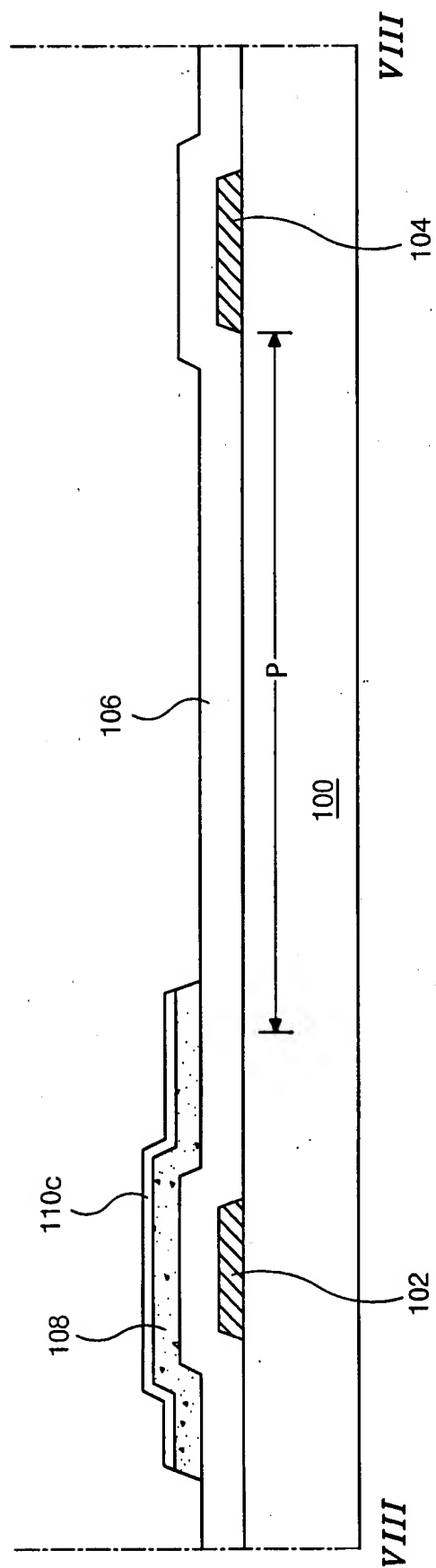


FIG. 8B

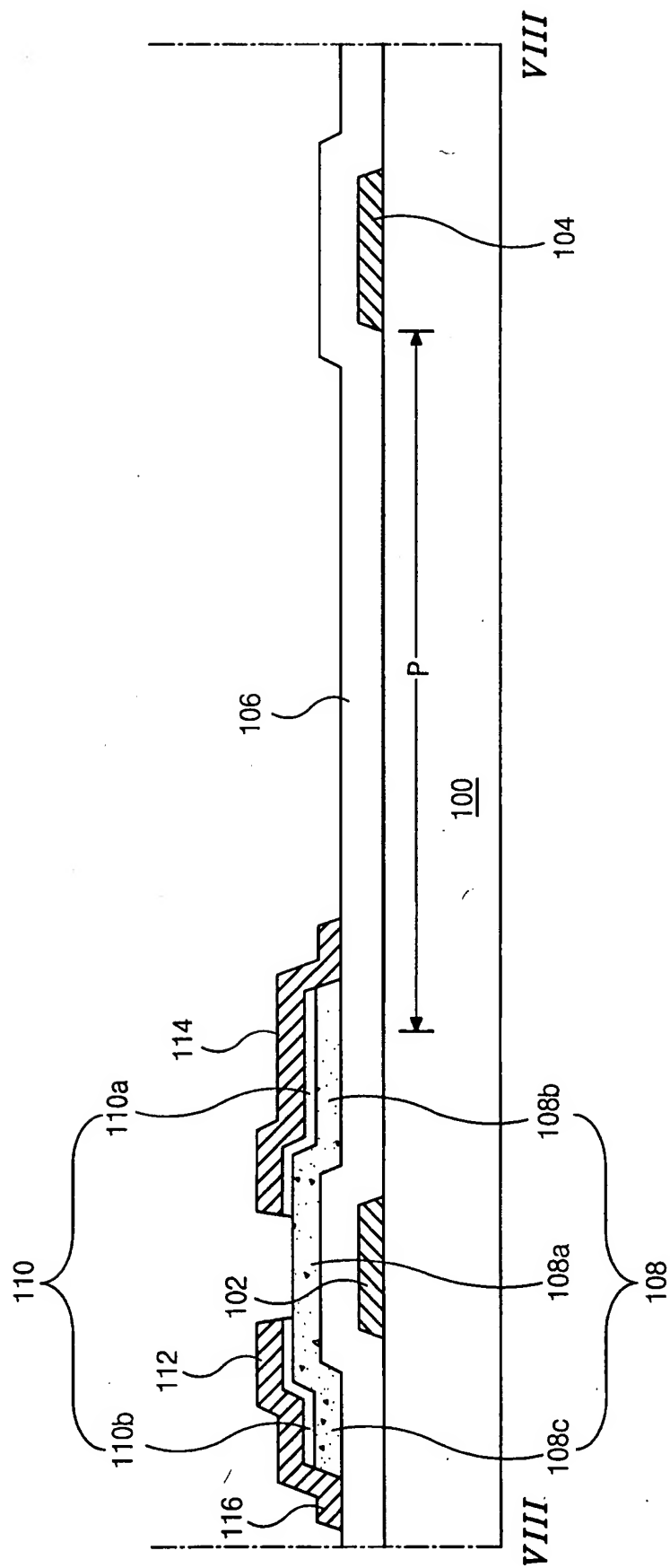


FIG. 8C

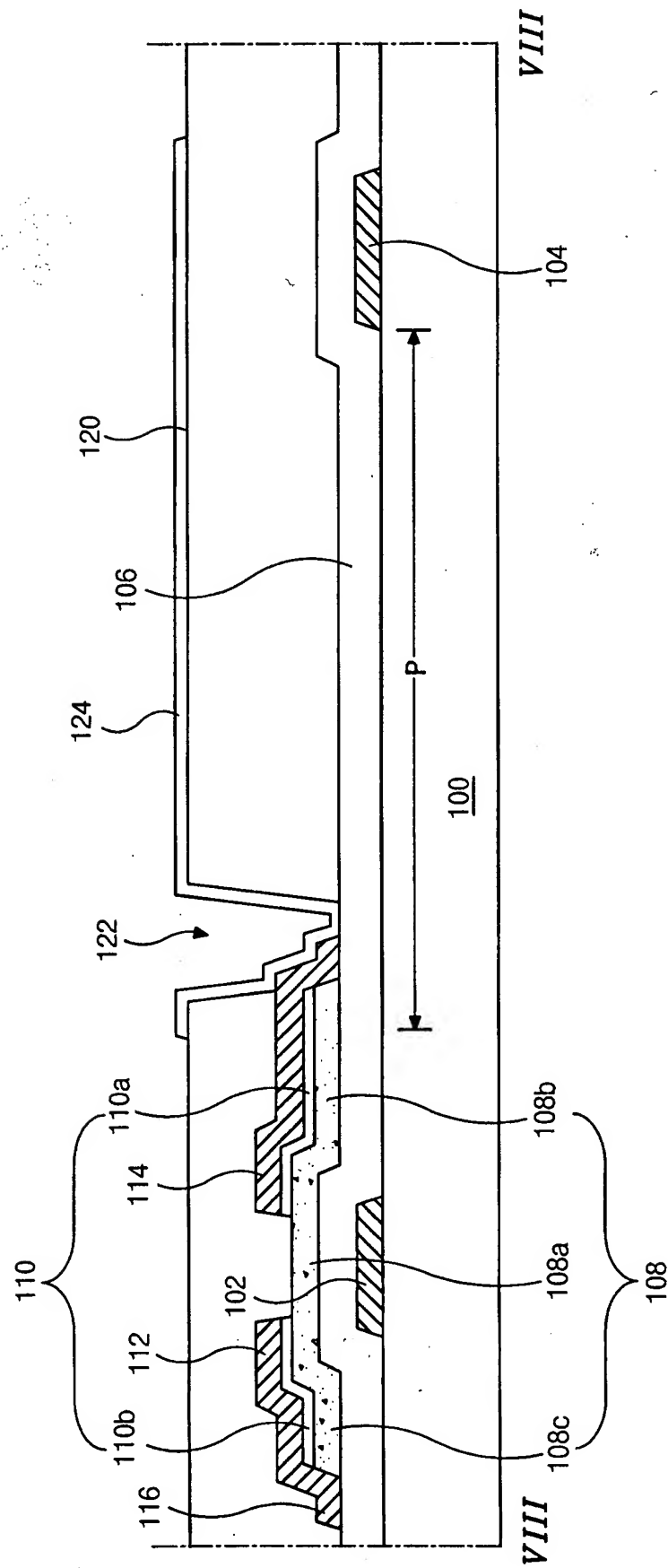


FIG. 9A

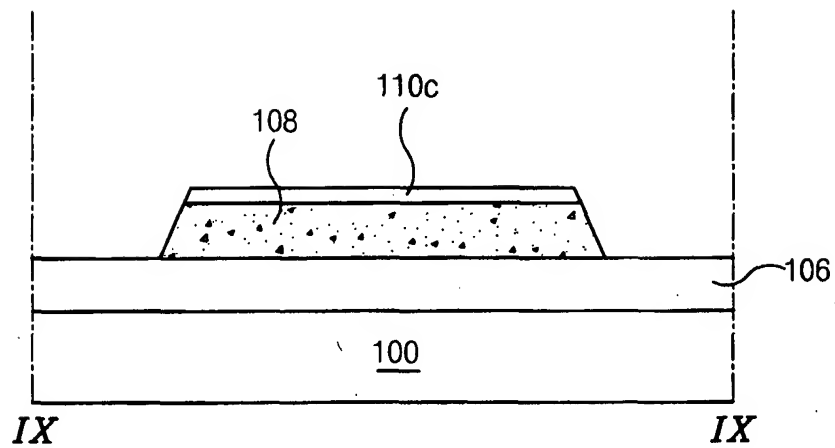


FIG. 9B

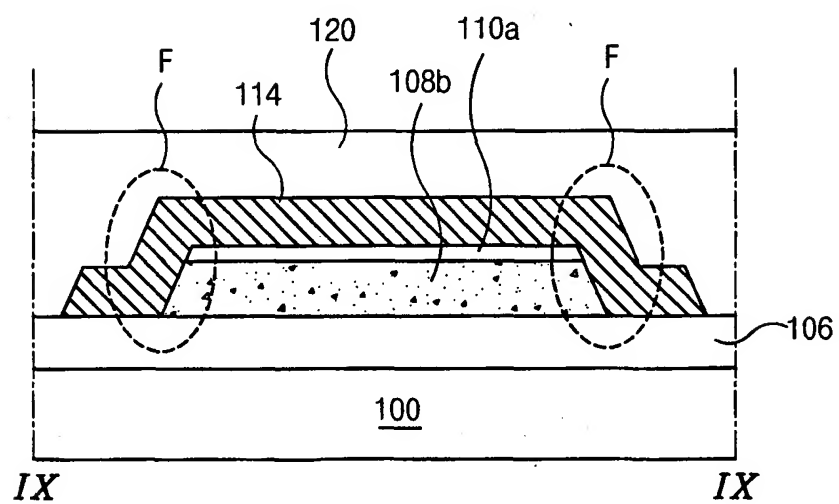


FIG. 9C

